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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLN. OF: ASPAR et al.
SERIAL NO.: 09/777,516
FILED: February 6, 2001
FOR: A Method of Producing a Thin Layer of Semiconductor Material
GROUP: 2823
EXAMINER: FOURSON III, GEORGE
DOCKET: BREV 12370 CON3

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Dear Sir:

In connection with the above-entitled matter, Applicants hereby proffer U.S. Patent Office Form PTO-1449, including copies of the references listed therein. These references came to applicants' attention in connection with litigation concerning a related U.S. Patent. The claims in the present application are believed to be patentably distinguished over these references.

This Supplemental Information Disclosure Statement is being made pursuant to the duty of disclosure imposed by law and formulated in 37 CFR 1.56(A). No representation is made that the information thus disclosed in fact constitutes prior art or that it is the closest prior art, inasmuch as 37 CFR 1.56(A) relies on a materiality concept which depends on subjectivity.


This Supplemental Information Disclosure Statement is being filed prior to the issuance of a further action following the filing of the Request for Continuation of Examination.

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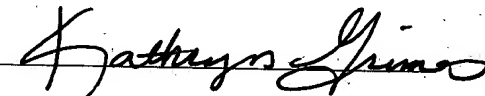
Therefore, we believe there are no fees involved with this Information Disclosure Statement. In the event there are additional fees payable, please charge them to our Deposit Account No. 08-1391.

Respectfully submitted,


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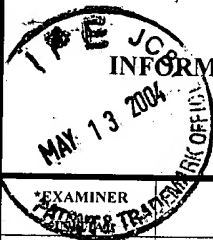
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INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Docket Number (Optional)

BREV 12370 CON3

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Applicant(s)

ASPAR et al.

Filing Date

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Group Art Unit

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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

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"High Fluence Retention of Noble Gases Implanted in Silicon" Wittmaack et al., *Radiation Effects*, Volume 39, 1978, pgs. 81-95

EXAMINER

DATE CONSIDERED

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.